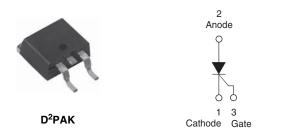
Vishay Semiconductors

Thyristor Surface Mount, Phase Control SCR, 8 A



PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
Diode variation	Single SCR							
I _{T(AV)}	8 A							
V _{DRM} /V _{RRM}	800 V							
V _{TM}	1.2 V							
I _{GT}	15 mA							
TJ	- 40 to 125 °C							

FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Designed and qualified according JEDEC-JESD47
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Input rectification and crow-bar (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-12TTS08SPbF High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS							
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS				
Capacitive input filter $T_A = 55 \text{ °C}$, $T_J = 125 \text{ °C}$, common heatsink of 1 °C/W	13.5	17	A				

MAJOR RATINGS AND CHARACTERISTICS								
PARAMETER	TEST CONDITIONS	VALUES	UNITS					
I _{T(AV)}	Sinusoidal waveform	8	A					
I _{T(RMS)}		12.5	A					
V _{RRM} /V _{DRM}		800	V					
I _{TSM}		110	А					
V _T	8 A, T _J = 25 °C	1.2	V					
dV/dt		150	V/µs					
dl/dt		100	A/µs					
TJ	Range	- 40 to 125	°C					

VOLTAGE RATINGS			
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA
VS-12TTS08SPbF	800	800	1.0

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HALOGEN

FREE



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VS-12TTS08SPbF Series

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PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	UNITS
Maximum average on-state current	I _{T(AV)}	т 100.00 г		8	
Maximum RMS on-state current	I _{T(RMS)}	$T_{\rm C} = 108$ °C,	180° conduction, half sine wave	12.5	•
Maximum peak one-cycle		10 ms sine pu	llse, rated V_{RRM} applied, $T_J = 125 \text{ °C}$	95	A
non-repetitive surge current	I _{TSM}	10 ms sine pulse, no voltage reapplied, T_J = 125 °C		110	
Maximum I ² t for fusing	l ² t	10 ms sine pu	llse, rated V_{RRM} applied, $T_J = 125 \text{ °C}$	45	A ² s
Maximum 1-t for fusing	1-1	10 ms sine pu	64	A-S	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 7	640	A²√s	
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °	1.2	V	
On-state slope resistance	r _t			16.2	mΩ
Threshold voltage	V _{T(TO)}	T _J = 125 °C		0.87	V
Maximum reverse and direct lockage current	1 /1	T _J = 25 °C		0.05	
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	V _R = Rated V _{RRM} /V _{DRM}	1.0	
Typical holding current	Ι _Η	Anode supply T _J = 25 °C	30	mA	
Maximum latching current	١ _L	Anode supply	50		
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max., I$	linear to 80 %, $V_{DRM} = R_g - k = Open$	150	V/µs
Maximum rate of rise of turned-on current	dl/dt			100	A/µs

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak gate power	P _{GM}		8.0	W				
Maximum average gate power	P _{G(AV)}		2.0	vv				
Maximum peak positive gate current	+ I _{GM}		1.5	А				
Maximum peak negative gate voltage	- V _{GM}		10	V				
	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 65 °C	20	mA				
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \ ^{\circ}C$	15					
		Anode supply = 6 V, resistive load, T_J = 125 °C	10					
		Anode supply = 6 V, resistive load, T_J = - 65 °C	1.2					
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	1					
		Anode supply = 6 V, resistive load, T_J = 125 °C	0.7	V				
Maximum DC gate voltage not to trigger	V_{GD}	T 125 °C V Batad value	0.2					
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA				

SWITCHING									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8						
Typical reverse recovery time	t _{rr}	T _J = 125 °C	3	μs					
Typical turn-off time	tq	ij= 125 C	100						

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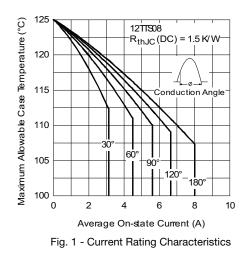
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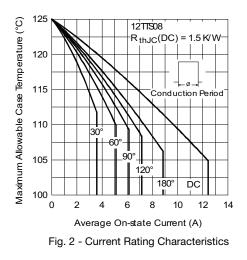
VS-12TTS08SPbF Series

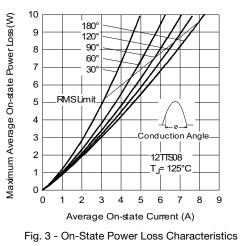


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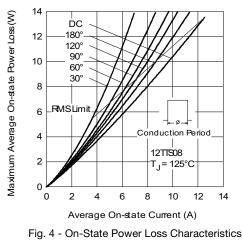
THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Maximum junction and sto temperature range	rage	T _J , T _{Stg}		- 40 to 125	°C			
Maximum thermal resistan junction to case	· · · · · · · · · · · · · · · · · · ·		DC operation	1.5				
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W			
Typical thermal resistance case to heatsink	,	R _{thCS}	Mounting surface, smooth and greased	0.5				
Approvimete weight				2	g			
Approximate weight				0.07	oz.			
Mounting torgue	minimum			6 (5)	kgf ⋅ cm			
Mounting torque —	maximum			12 (10)	(lbf · in)			
Marking device			Case style D ² PAK (SMD-220)	12TT	S08S			











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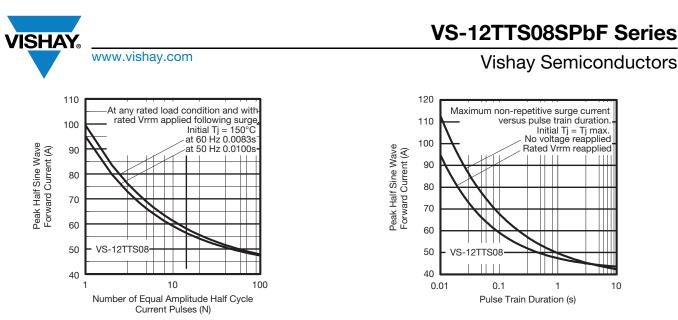


Fig. 5 - Maximum Non-Repetitive Surge Current

Fig. 6 - Maximum Non-Repetitive Surge Current

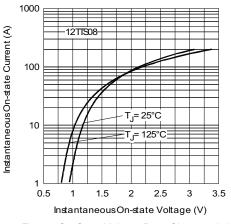


Fig. 7 - On-State Voltage Drop Characteristics

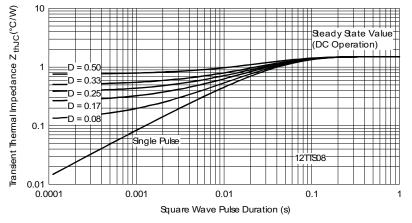


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



• TRR = Tape and reel (right oriented)

PbF = Lead (Pb)-free

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ORDERING INFORMATION (Example)									
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION						
VS-12TTS08SPbF	50	1000	Antistatic plastic tubes						
VS-12TTS08STRRPbF	800	800	13" diameter reel						
VS-12TTS08STRLPbF	800	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95046						
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						

VS-12TTS08SPbF Series

Vishay Semiconductors



ORDERING INFORMATION TABLE

Device code	VS-	12	т	т	S	08	S	TRL	PbF
		2	3	4	5	6	7	8	9
	1 - 2 -			niconduo ng (12.5	•	oduct			
	3 -	Circ	uit conf	iguratior hyristor					
	4 -		kage: TO-220	AC					
	5 -		e of silio Standa	con: rd recov	ery rect	ifier			
	6 - 7 -		-	ng (08 =) D ² PAK	-		rsion		
	8 -		one = Tu RL = Tap	ube be and re	eel (left	orienteo	d)		

Outline Dimensions

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D²PAK



Conforms to JEDEC outline D²PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 (|(0.38)^{MIN.} (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)^{0.01} Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Ċ 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIMETERS		INCHES		HES NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3 0.25 BSC 0.010 BSC		BSC			
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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DIMENSIONS in millimeters and inches



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